XC62E series is Not Recommended for New Designs. XC62E Series

ETR0311_005a

Boosting Voltage Regulators

■GENERAL DESCRIPTION

The XC62E series are a group of positive output voltage regulators that can supply up to 1A of output current using an external transistor. Low power and high accuracy are achieved through CMOS process and laser trimming technologies. The series consists of a high precision voltage reference, an error correction circuit and a short-circuit protected output driver.

In stand-by mode, supply current can be dramatically cut. Since the input-output voltage differential is small, loss control efficiency is good.

The XC62E is particularly suited for use with battery operated portable products, and products where supply current regulation is required.

The series are available in an ultra small SOT-25 package.

In connection with the CE function, apart from the negative logic XC62EP series, a positive logic XC62ER series (custom) is also available.

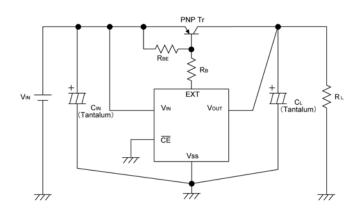
■ APPLICATIONS

- Portable cameras and video recorders
- Battery powered equipment
- Palmtops
- Reference voltage sources

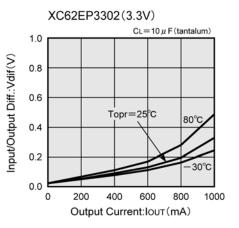


Dropout Voltage	: 0.1A@100mA (Performance depends on the external transistor characteristics.)				
Maximum Output Current	t : 1000mA				
Output Voltage Range	:1.5V~6.0V in 100mV increments				
Highly Accurate	: Setting voltage ±2%				
Low Power Consumption	n : 50 μ Α (Vout=5.0V) (TYP.)				
	: 0.2 µ A (Stand-by) (TYP.)				
Output Voltage Tempera	ture Characteristics				
	: ±100ppm/ °C (TYP.)				
Line Regulation	: 0.1%/V (TYP.)				
CMOS Low Power Consumption					
Package Environmentally Friendly	: SOT-25 : EU RoHS Compliant				

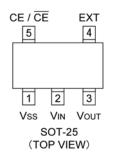
■TYPICAL APPLICATION CIRCUIT



■ TYPICAL PERFORMANCE CHARACTERISTICS



■ PIN CONFIGURATION



■ PIN ASSIGNMENT

PIN NUMBER	PIN NAME	FUNCTION
1	Vss	Ground
2	Vin	Supply Voltage Input
3	Vout	Regulated Voltage Output
4	EXT	Base Current Control
5	CE/CE	Chip Enable

FUNCTION

SERIES	CE OUTPUT VOLTAG	
XC62ER	Н	ON
ACOZER	L	OFF
XC62EP	Н	OFF
	L	ON

H=High level L=Low level

L=LOW level

■ PRODUCT CLASSIFICATION

Ordering Information

XC62E1234567-8 (*1)

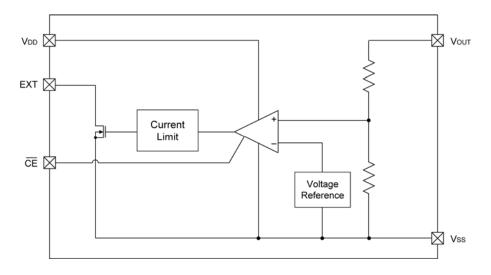
DESIGNATOR	DESCRIPTION	SYMBOL	DESCRIPTION
1			Positive
U	CE Pin Logic	Р	Negative
23	Output Voltage	15 ~ 60	e.g. Vout 1.5V→②=1, ③=5 Vout 6.0V→②=6, ③=0
4	Temperature Characteristics	0	±100ppm (TYP.)
5	Output Voltage Accuracy	2	±2%
	Packages	MR	SOT-25
67-8	Taping Type (*2)	MR-G	SOT-25

(*1) The "-G" suffix indicates that the products are Halogen and Antimony free as well as being fully RoHS compliant.

^('2) The device orientation is fixed in its embossed tape pocket. For reverse orientation, please contact your local Torex sales office or representative. (Standard orientation: (BR-(B), Reverse orientation: (BL-(B)))

Ta = 25°C

■BLOCK DIAGRAM



■ABSOLUTE MAXIMUM RATINGS

PARAMETER SYMBOL RATINGS UNITS **VIN Input Voltage** Vin 12.0 V Vout Output Voltage Vout Vss-0.3~VIN+0.3 V CE/CE Input Voltage Vss-0.3~VIN+0.3 V VCE V EXT Output Voltage Vext 12.0 EXT Output Current 50 IEXT mΑ Pd 150 mW **Power Dissipation** °C **Operating Temperature Range** Topr -30~+80 °C Storage Temperature Range -40~+125 Tstg

■ ELECTRICAL CHARACTERISTICS

XC62EP3002 VOUT(T)=3.0V (*1)						Ta=25°C
PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Output Voltage	Vout(e) ^(*2)	IOUT=50mA VIN=4.0V	2.940	3.000	3.060	V
Maximum Output Current*	IOUT max	VIN=4.0V	-	1000	-	mA
Load Regulation ^(*6)	Δνουτ	Vin=4.0V 1mA≦Iout≦100mA	-60	-	60	mV
Dropout Voltage (*3)	Vdif	IOUT=100mA	-	100	-	mV
Supply Current 1	ISS1	VIN=4.0V, VCE=VSS	-	50	80	μA
Supply Current 2	ISS2	VIN=8.0V,VCE=VIN	-	-	0.6	μA
Line Regulation (*6)	$\frac{\Delta VOUT}{\Delta VIN \cdot VOUT}$	lout=50mA 4.0V≦ViN≦8.0V	-	0.1	0.3	%V
Input Voltage	ΔVin		-	-	8.0	V
Output Voltage Temperature Characteristics (*6)	<u>ΔVouτ</u> ΔTopr ⋅ Vouτ	lou⊤=10mA -30°C≦Topr≦80°C	-	±100	-	ppm/°C
EXT Output Voltage	Vext		-	-	8.0	V
EXT Leak Current	ILEAK		-	-	0.5	μA
CE "High" Level Voltage	Vсен		1.5	-	-	V
CE "Low" Level Voltage	VCEL		-	-	0.25	V
CE "High" Level Current	Ісен	VCE=VIN	-	-	0.1	μA
CE "Low" Level Current	ICEL	VCE=VSS	-0.2	-0.05	0	μA

The characteristics for the XC62ER series are the same as above except for the CE operating logic, which is the opposite.

NOTE:

- *1: VOUT(T)=Specified output voltage.
- *2: VOUT(E)=Effective output voltage (i.e. the output voltage when "VOUT(T)+1.0V" is provided at the VIN pin while maintaining a certain IOUT value).
- *3: Vdif= {VIN1 (*5)-VOUT1 (*4)}
- *4: VOUT1= A voltage equal to 98% of the output voltage whenever an amply stabilized IOUT {VOUT(T)+1.0V} is input.
- *5: VIN1=The input voltage when VOUT1 appears as input voltage is gradually decreased.
- *6: The characteristics for the parameters are liable to vary depending on which transistor is used. Please use a transistor with a low saturation voltage level and hFE equal to 100 or more.
- *7: The maximum output current value is not a value representing continuous output due to the limitations of the 2AS1213 transistor's power dissipation.

■ ELECTRICAL CHARACTERISTICS (Continued)

XC62EP4002 VOUT(T)=4.0V(*1)					Ta=25°C
PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Output Voltage	Vout(e) (*2)	Iout=50mA Vin=5.0V	3.920	4.000	4.080	V
Maximum Output Current (*6)	IOUT max	VIN=5.0V	-	1000	-	mA
Load Regulation ^(*6)	Δνουτ	Vin=5.0V 1mA≦Iout≦100mA	-60	-	60	mV
Dropout Voltage (*3)	Vdif	IOUT=100mA	-	100	-	mV
Supply Current 1	ISS1	VIN=5.0V, VCE=VSS	-	50	80	μA
Supply Current 2	ISS2	VIN=8.0V,VCE=VIN	-	-	0.6	μA
Line Regulation (*6)	ΔVout ΔVin • Vout	loυτ=50mA 5.0V≦Vιν≦8.0V	-	0.1	0.3	%V
Input Voltage	VIN		-	-	8.0	V
Output Voltage Temperature Characteristics ^(*6)	ΔVουτ ΔTopr • Voυτ	lou⊤=10mA -30°C≦Topr≦80°C	-	±100	-	ppm/°C
EXT Output Voltage	VEXT		-	-	8.0	V
EXT Leak Current	ILEAK		-	-	0.5	μA
CE "High" Level Voltage	VCEH		1.5	-	-	V
CE "Low" Level Voltage	VCEL		-	-	0.25	V
CE "High" Level Current	Ісен	VCE=VIN	-	-	0.1	μA
CE "Low" Level Current	ICEL	VCE=VSS	-0.2	-0.05	0	μA

XC62EP4002 VOUT(T)=5.0V(*1)

Ta=25°C

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)					1a=25 C
SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
V _{OUT(E)} (*2)	Iout=50mA Vin=6.0V	4.940	5.000	5.100	V
IOUT max	VIN=6.0V	-	1000	-	mA
ΔVουτ	Vin=6.0V 1mA≦Iout≦100mA	-60	-	60	mV
Vdif	IOUT=100mA	-	100	-	mV
ISS1	VIN=6.0V, VCE=VSS	-	50	80	μΑ
ISS2	VIN=8.0V,VCE=VIN	-	-	0.6	μΑ
ΔVout ΔVin • Vout	loυτ=50mA 6.0V≦Vιν≦8.0V	-	0.1	0.3	%V
Vin		-	-	8.0	V
∆Vоит ∆Topr • Vouт	lou⊤=10mA -30°C≦Topr≦80°C	-	±100	-	ppm/°C
Vext		-	-	8.0	V
ILEAK		-	-	0.5	μΑ
VCEH		1.5	-	-	V
VCEL		-	-	0.25	V
Ісен	VCE=VIN	-	-	0.1	μA
ICEL	VCE=VSS	-0.2	-0.05	0	μA
	SYMBOL VOUT(E) (*2) IOUT max △VOUT Vdif ISS1 ISS2 △VOUT △VIN • VOUT VIN △VOUT △TOPT • VOUT VEXT ILEAK VCEH VCEL ICEH	SYMBOLCONDITIONS $V_{OUT(E)}$ (*2)IOUT=50mA VIN=6.0VIOUT maxVIN=6.0V $\Delta VOUT$ VIN=6.0V $\Delta VOUT$ IOUT=100mAVdifIOUT=100mAISS1VIN=6.0V, VCE=VSSISS2VIN=8.0V, VCE=VIN $\Delta VOUT$ IOUT=50mA $\Delta VOUT$ 6.0V $\leq VIN \leq 8.0V$ VINVIN $\Delta VOUT$ IOUT=10mA $\Delta VOUT$ IOUT=10mA $\Delta VOUT$ IOUT=10mA ∇VIN ·30°C \leq Topr $\leq 80°C$ VEXTILEAKVCEHVCE=VINICEHVCE=VIN	SYMBOLCONDITIONSMIN. $V_{OUT(E)}$ (*2)IOUT=50mA VIN=6.0V4.940IOUT maxVIN=6.0V- Δ VOUTVIN=6.0V 1mA \leq IOUT \leq 100mA-60VdifIOUT=100mA-VsisVIN=6.0V, VCE=VSS-ISS1VIN=6.0V, VCE=VIN- Δ VOUTIOUT=50mA 6.0V \leq VIN \leq 8.0V- Δ VOUTIOUT=50mA Δ VOUTIOUT=10mA -30°C \leq Topr \leq 80°C-VEXTILEAKVCEH1.5-VCELICEHVCE=VIN-	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $

The characteristics for the XC62ER series are the same as above except for the CE operating logic, which is the opposite.

Note: *1. VOUT(T)=Specified output voltage.

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*3. Vdif= {VIN1 (*5)-VOUT1 (*4)}

*4. VOUT1= A voltage equal to 98% of the output voltage whenever an amply stabilized IOUT {VOUT(T)+1.0V} is input.

*5. VIN1= The input voltage when VOUT1 appears as input voltage is gradually decreased.

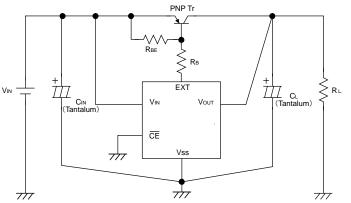
*6. The characteristics for the parameters are liable to vary depending on which transistor is used.

Please use a transistor with a low saturation voltage level and hFE equal to 100 or more. *7. The maximum output current value is not a value representing continuous output due to the limitations of the 2AS1213

transistor's power dissipation.

TYPICAL APPLICATION CIRCUIT





External Components: PNP Tr.: 2SA1213 RBE: $20k\Omega \sim 47k\Omega$ RB: Please refer to Note 2 on the following page. CIN: 10μ F (Tantalum) CL: 47μ F (Tantalum) 10μ F minimum

■OPERATIONAL EXPLANATION

Output voltage (VOUT) can be fixed by revising the external transistor's base current. This can be done by comparing the detected voltage level and the setting voltage power supply level.

With the XC62EP (CE negative voltage), if a voltage above the \overline{CE} pin's "H" level is applied, the IC will enter stand-by mode where the base and differential amplifier's currents are regulated.

■NOTES ON USE

1. PNP Transistor

The selection of a transistor should take into account output current, input voltage and power dissipation for each specific application. It is recommended that a transistor that has a low output saturated voltage (VCE) and high hFE characteristics be used.

2. RB Resistor

Although the IC unit is protected by a base current remitter circuit, it is recommended that a resistor (RB) be connected between the transistor's base and the IC's EXT pin to protect the transistor.

Required output current can be calculated using the following equation although characteristic variations and conditions of use should be carefully checked before use. The following equation also indicates the conditions needed to obtain IOUT (MAX.) at VIN (MIN.). However, the larger the input current, the larger the output current (IOUT) that can be obtained.

$$\frac{V_{IN}(MIN.)-1.2(V)}{R_B}$$
 $\frac{0.7(V)}{R_{BE}}$ $>$ $\frac{IOUT(MAX.)}{hFE}$

3. RBE Resistor, CL Capacitor

To prevent oscillation due to output load variation, use of a phase compensation capacitor CL is recommended. Please use a Tantalum capacitor of at least 10mF. Please also use an RBE resistor of less than $47k\Omega$.

An RBE resistor of between 20k $\Omega~$ and 47k $\Omega~$ is recommended for less power consumption.

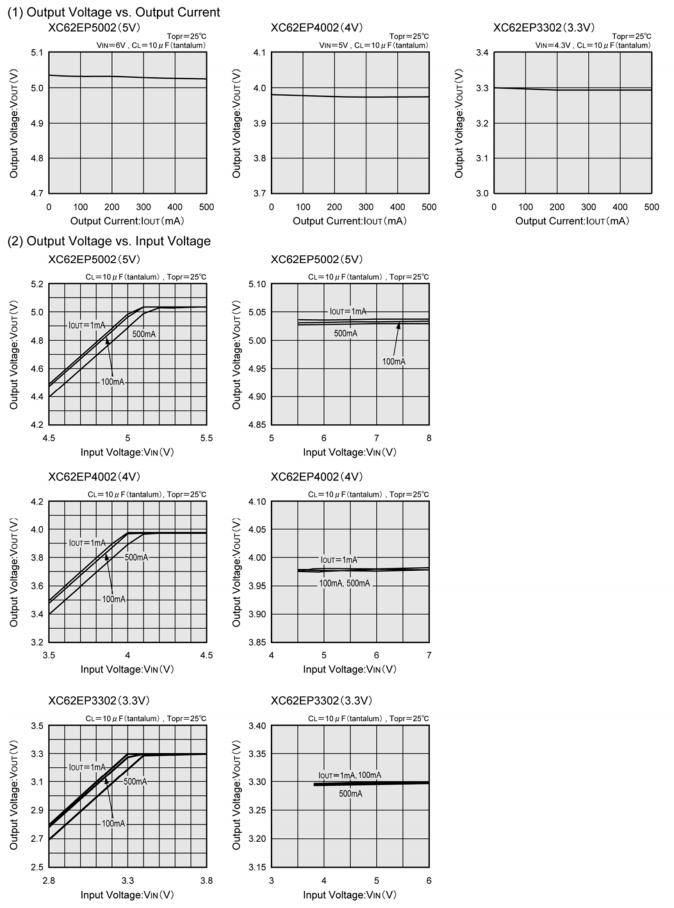
4. Input Impedance

In order to control oscillation brought about as a result of impedance at the power supply line, connect a capacitor of $10 \,\mu$ F or more (Tantalum) between the external transistor's emitter and the ground pin.

Protection Circuit

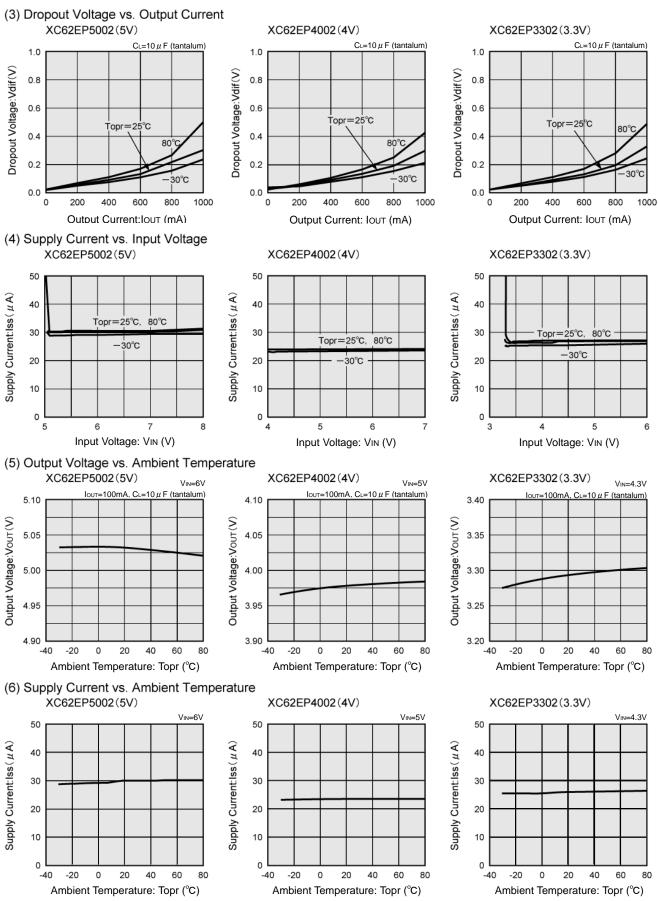
The built-in protection circuit is to protect the IC only. Therefore to prevent output shorts and overshoot current through the transistor, use of a resistor RB or an overshoot current protection circuit is recommended. Care should also be taken with the transistor's power dissipation.





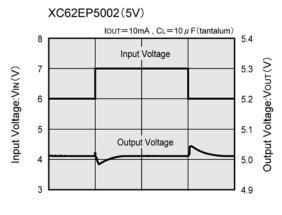
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■TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

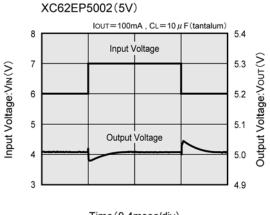


TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

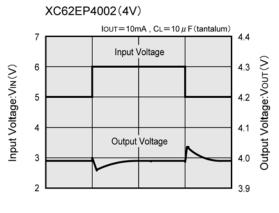
(7) Input Transient Response



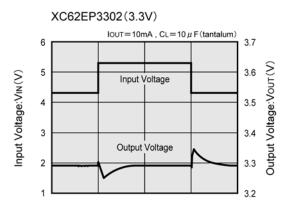
Time(0.4msec/div)



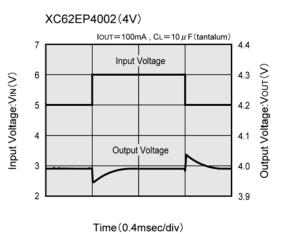
Time(0.4msec/div)

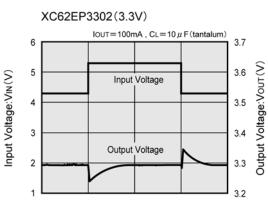






Time(0.4msec/div)

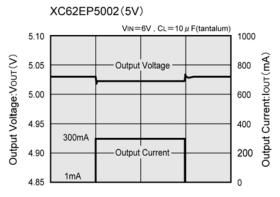


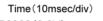


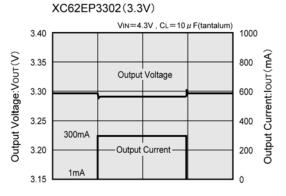
Time(0.4msec/div)

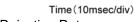
TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

(8) Load Transient Response

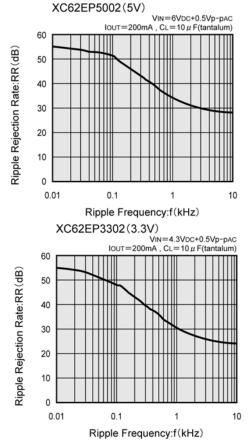


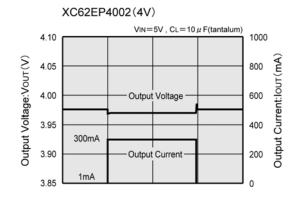




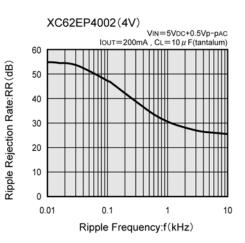


(9) Ripple Rejection Rate



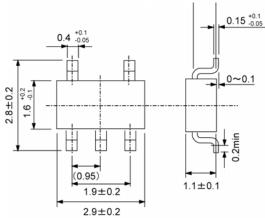


Time(10msec/div)



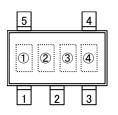
■ PACKAGING INFORMATION





■MARKING RULE

●SOT-25



SOT-25 (TOP VIEW)

1 not used

② represents integer of output voltage

MARK (XC62ER Type)	VOLTAGE (V)	MARK (XC62EP Type)	VOLTAGE (V)
2	2.x	2	2.x
3	3.x	3	3.x
4	4.x	4	4.x
5	5.x	5	5.x
6	6.x	6	6.x

③ represents decimal number of output voltage

MARK (XC62ER Type)	VOLTAGE (V)	MARK (XC62EP Type)	VOLTAGE (V)
0	x.0	0	x.0
1	x.1	1	x.1
2	x.2	2	x.2
3	x.3	3	x.3
4	x.4	4	x.4
5	x.5	5	x.5
6	x.6	6	x.6
7	x.7	7	x.7
8	x.8	8	x.8
9	x.9	9	x.9

4 based on internal standards

XC62E Series

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